

BYC30MX-650P

Hyperfast power diode Rev.01 - 16 September 2022

Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO220F plastic package.



2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

| Symbol | Parameter | Conditions | Notes | s Values | | | Unit |
|---|------------------------------------|---|-------|----------|------|------|------|
| Absolute | maximum rating | | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | | | 650 | | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2 | | 30 | | | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; $t_{\rm p}$ = 25 $\mu s;$ square-wave pulse | | | 60 | | A |
| I _{FSM} non-repetitive peak forward current | | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3 | | 270 | | | A |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | | | 297 | | А |
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 5</u> | | - | 2.05 | 2.75 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 5</u> | | - | 1.38 | 1.80 | V |
| Dynamic | characteristics | | | | | | |
| t _{rr} | reverse recovery time | I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _i = 25 °C; <u>Fig. 6</u> | | - | 20 | 24 | ns |

5. Pinning information

| Table 2. F | inning infor | mation | | |
|------------|--------------|------------------------------------|--------------------|--------------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | K | cathode | | |
| 2 | А | anode | 000 | K — A 001aaa020 |
| mb | mb | mounting base; connected to cathod | | |

6. Ordering information

| Table 3. Ordering information | | | | | | | | | |
|-------------------------------|-----------------|-----------------------|----------------|---------------------------|-----------------|-----------------------|--|--|--|
| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date | | | |
| BYC30MX-650P | TO220F-2L | BYC30MX-650PQ | Tube | 50 | TO220Fd-2L | 02-Aug-2022 | | | |

7. Marking

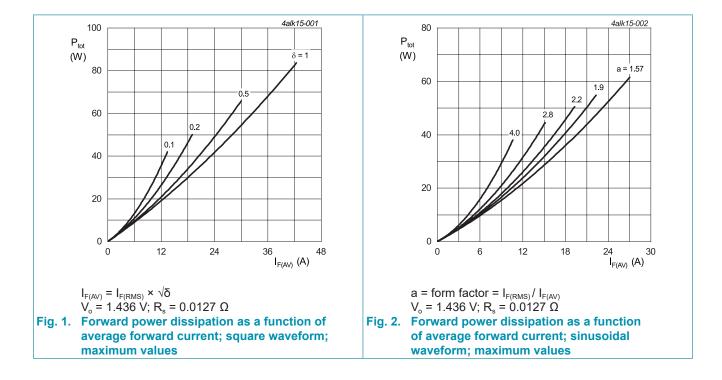
| Table 4. Marking codes | | |
|------------------------|-----------------|--|
| Type number | Marking codes | |
| BYC30MX-650P | BYC30MX 650P | |

8. Limiting values

Table 5. Limiting values

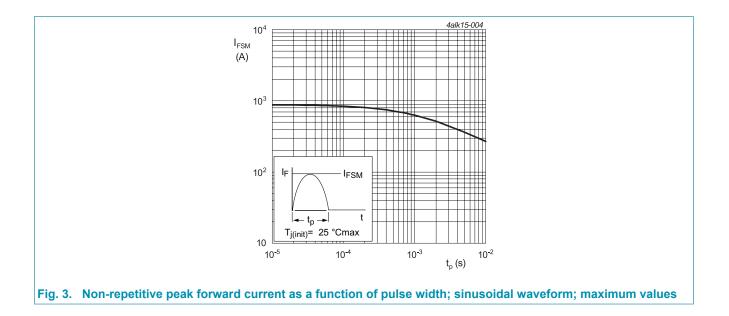
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|--------------------|--|---|-------|------------|------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V _R | reverse voltage | DC | | 650 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> | | 30 | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; $t_{\rm p}$ = 25 μs ; square-wave pulse | | 60 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3 | | 270 | A |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | | 297 | А |
| T _{stg} | storage temperature | | | -65 to 175 | °C |
| T _j | junction temperature | | | -65 to 175 | °C |



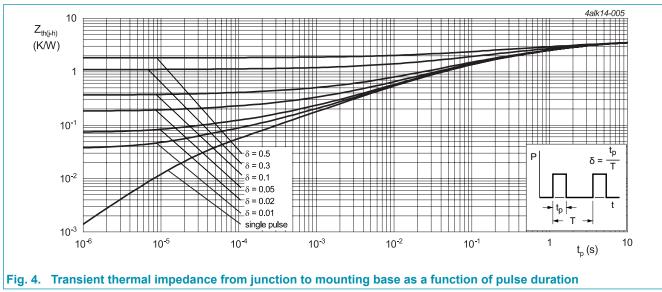
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BYC30MX-650P Hyperfast power diode



9. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
|-----------------------|--|---------------|-------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | <u>Fig. 4</u> | | - | - | 3.5 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |

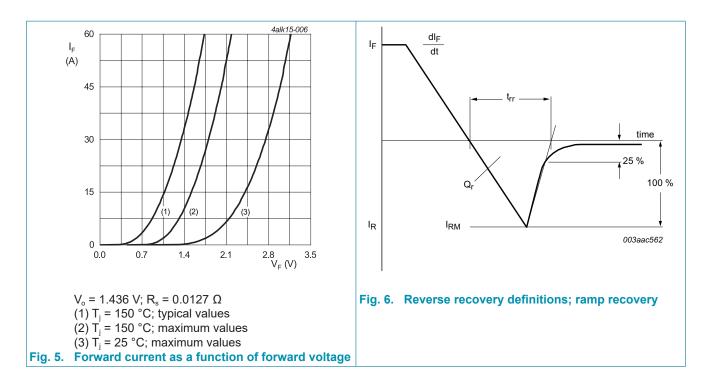


10. Isolation characteristics

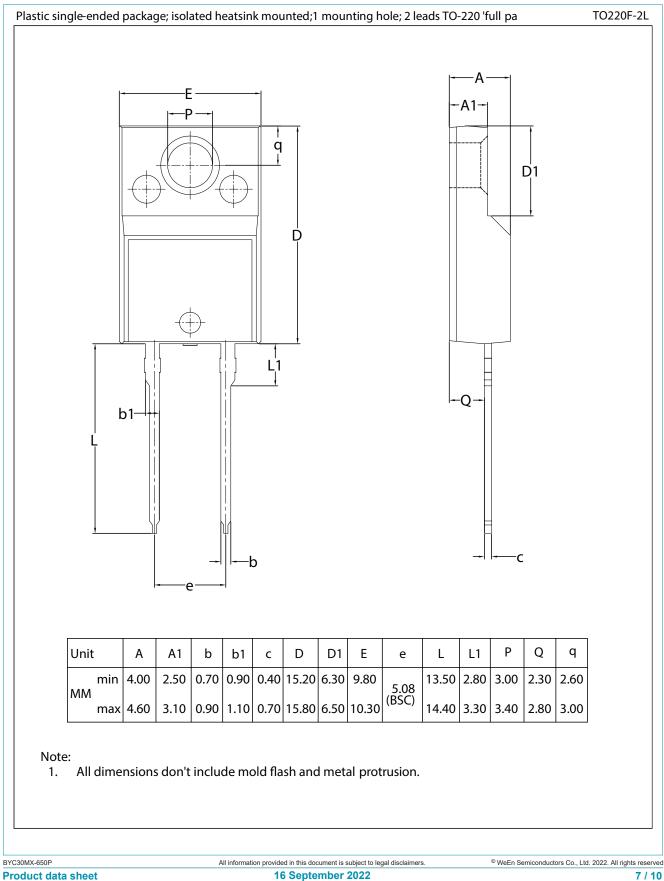
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------------|-----------------------|---|-----|-----|------|------|
| $V_{\text{isol}(\text{RMS})}$ | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | f = 1 MHz; from cathode to external heatsink | - | 10 | - | pF |

11. Characteristics

| | haracteristics | | | 1 | | | |
|-----------------------|---|--|-------|-----|------|------|------|
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 5</u> | | - | 2.05 | 2.75 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 5</u> | | - | 1.38 | 1.80 | V |
| I _R revers | reverse current | V _R = 650 V; T _j = 25 °C | | - | 0.6 | 30 | μA |
| | | V _R = 650 V; T _j = 150 °C | | - | 0.25 | 1 | mA |
| Dynamic | characteristics | 1 | | , | | | |
| Q _r | reverse charge | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 6}$ | | - | 68 | - | nC |
| | | I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 6</u> | | - | 330 | - | nC |
| t _{rr} r | reverse recovery time | I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 6</u> | | - | 20 | 24 | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 6}$ | | - | 38 | - | ns |
| | | I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 6</u> | | - | 73 | - | ns |
| cur | peak reverse recovery currentnon-repetitive | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 6}$ | | - | 3.7 | - | A |
| | avalanche energy | I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 6</u> | | - | 9.1 | - | A |
| E _{as} | non-repetitive avalanche energy | I _R = 2 A; L = 15 mH; T _{j(init)} = 25 °C | | 30 | - | - | mJ |



12. Package outline



BYC30MX-650P

Hyperfast power diode

13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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